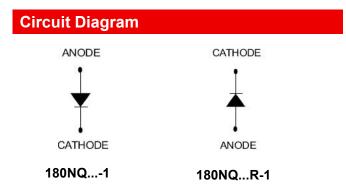






180NQ035/R-1 180NQ040/R-1 180NQ045/R-1 SCHOTTKY RECTIFIER





Features

- 150 °C TJ operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5' S
- Easier to mount and lower profile than DO-5' S
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	35	180NQ035(R)-1	
Working Peak Reverse Voltage DC Blocking Voltage	V _{RWM} VR		40 45	180NQ040(R)-1 180NQ045(R)-1	V
Average Forward Current	IF(AV)	50% duty cycle @Tc =90°C, rectangular wave form	180		А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	3480		А
Non-Repetitive Avalanche Energy	Eas	TJ=25℃,IAS=36A,L=0.37mH	243		mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T _J max. V _A =1.5×V _R typical	36		A

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 180A, Pulse, T _J = 25 °C @ 360A, Pulse, T _J = 25 °C	0.58 -	0.60 0.78	V
	V _{F2}	@ 180A, Pulse, T _J = 125 °C @ 360A, Pulse, T _J = 125 °C	0.50 -	0.56 0.75	V
Reverse Current*	I _{R1}	$@V_R = rated V_R T_J = 25 \circ C$	0.3	15	mA
	I _{R2}	$@V_R = rated V_R T_J = 125 °C$	250	600	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	5800	7700	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{\star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

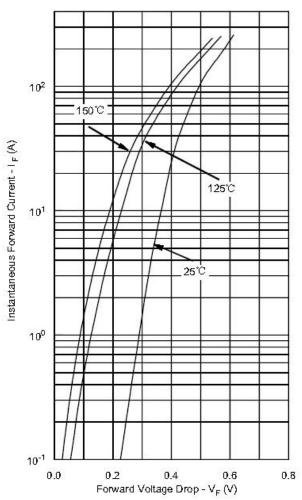
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifi	Units	
Junction Temperature	TJ	-	-55 to	°C	
Storage Temperature	T _{stg}	-	-55 to	Ο°	
Typical Thermal Resistance Junction to Case	$R_{ ext{ heta}JC}$	DC operation	0.30		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ hetacs}$	Mounting surface, smooth and greased	0.1	°C/W	
Mounting Torque	т	Non-lubricated threads	Mounting Torque	23(min) 29(max)	Kg-cm
	Тм		Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	25	g	
Case Style	PRM1-1				

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Ratings and Characteristics Curves

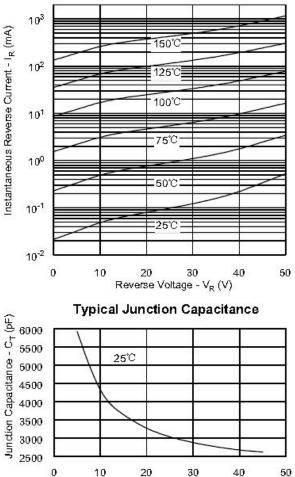


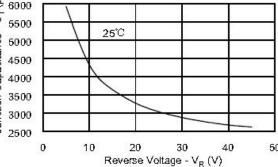
Typical Forward Characteristics

Typical Reverse Characteristics

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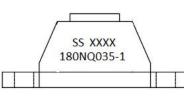


Ordering Information

Device Package		Shipping	
180NQ SERIES	PRM1-1(Pb-Free)	27pcs/ box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXX is YYWW

1st row	SS YYWW
2nd row	180NQ035-1
SS	= SS
YY	= Year
WW	= Week

Cautions: Molding resin Epoxy resin UL:94V-0

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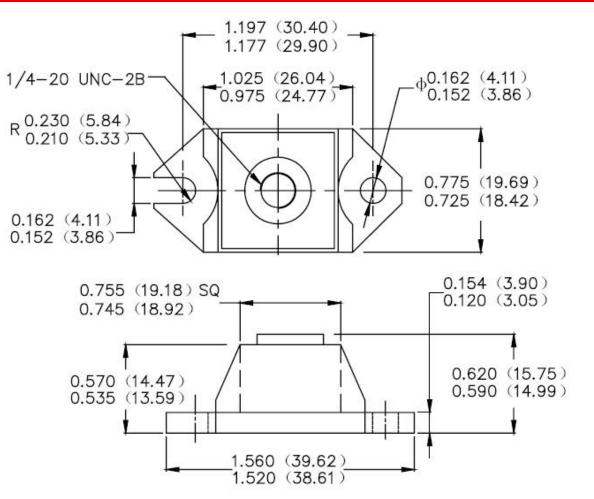


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Mechanical Dimensions PRM1-1 (Inches/Millimeters)









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